

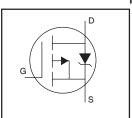
### **Features**

- Advanced Planar Technology
- Low On-Resistance
- P-Channel
- Dynamic dV/dT Rating
- 150°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified \*

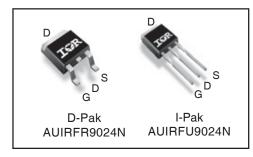
### Description

Specifically designed for Automotive applications, this Cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low onresistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.

# AUIRFR9024N AUIRFU9024N



H	HEXFET® Power MOSFET						
	$V_{(BR)DSS}$	-55V					
	R <sub>DS(on)</sub> max.	0.175Ω					
	I <sub>D</sub>	-11A					



G	D	S
Gate	Drain	Source

### **Absolute Maximum Ratings**

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature  $(T_A)$  is  $25^{\circ}$ C, unless otherwise specified.

	Parameter	Max.	Units
I <sub>D</sub> @ T <sub>C</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ -10V	-11	
I <sub>D</sub> @ T <sub>C</sub> = 100°C	Continuous Drain Current, V <sub>GS</sub> @ -10V	-8	Α
I <sub>DM</sub>	Pulsed Drain Current ①	-44	
P <sub>D</sub> @T <sub>C</sub> = 25°C	Power Dissipation	38	W
	Linear Derating Factor	0.30	W/°C
$V_{GS}$	Gate-to-Source Voltage	± 20	V
E <sub>AS</sub>	Single Pulse Avalanche Energy(Thermally limited) ②	62	mJ
I <sub>AR</sub>	Avalanche Current ①	-6.6	Α
E <sub>AR</sub>	Repetitive Avalanche Energy ①	3.8	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-10	V/ns
T <sub>J</sub>	Operating Junction and	-55 to + 150	
T <sub>STG</sub>	Storage Temperature Range		°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	

#### Thermal Resistance

	Parameter	Тур.	Max.	Units
$R_{\theta JC}$	Junction-to-Case		3.3	
$R_{\theta JA}$	Junction-to-Ambient (PCB mount) **		50	°C/W
$R_{\theta JA}$	Junction-to-Ambient		110	

HEXFET® is a registered trademark of International Rectifier.

<sup>\*</sup>Qualification standards can be found at http://www.irf.com/

### Static Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-55			V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient		-0.05		V/°C	Reference to 25°C, I <sub>D</sub> = -1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance			0.175	Ω	V <sub>GS</sub> = -10V, I <sub>D</sub> = -6.6A ④
$V_{GS(th)}$	Gate Threshold Voltage	-2.0		-4.0	V	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$
gfs	Forward Transconductance	2.5			S	$V_{DS} = -25V, I_{D} = -7.2A$ ©
I <sub>DSS</sub>	Drain-to-Source Leakage Current			-25	μΑ	$V_{DS} = -55V, V_{GS} = 0V$
				-250		$V_{DS} = -44V, V_{GS} = 0V, T_{J} = 150^{\circ}C$
I <sub>GSS</sub>	Gate-to-Source Forward Leakage			100	nA	$V_{GS} = -20V$
	Gate-to-Source Reverse Leakage			-100		$V_{GS} = 20V$

### Dynamic Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

		(				,
$Q_g$	Total Gate Charge			19		$I_{D} = -7.2A$
$Q_{gs}$	Gate-to-Source Charge			5.1	nC	$V_{DS} = -44V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge			10	Ī	V <sub>GS</sub> = -10V,See Fig 6 and 13 @6
t <sub>d(on)</sub>	Turn-On Delay Time		13			V <sub>DD</sub> = -28V
t <sub>r</sub>	Rise Time		55		Ī	$I_{D} = -7.2A$
t <sub>d(off)</sub>	Turn-Off Delay Time		23		ns	$R_G = 24 \Omega$
t <sub>f</sub>	Fall Time		37		Ī	$R_D = 3.7\Omega$ , See Fig.10 $@6$
L <sub>D</sub>	Internal Drain Inductance		4.5		nH	Between lead, 6mm (0.25in.)
L <sub>S</sub>	Internal Source Inductance		7.5			from package and center of die contact
C <sub>iss</sub>	Input Capacitance		350			V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance		170		рF	V <sub>DS</sub> = -25V
C <sub>rss</sub>	Reverse Transfer Capacitance		92		Ī	f = 1.0MHz,see Fig.5 ®

### **Diode Characteristics**

	Parameter	Min.	Тур.	Max.	Units	Conditions
Is	Continuous Source Current			-11		MOSFET symbol
	(Body Diode)			-11	Α	showing the
I <sub>SM</sub>	Pulsed Source Current			-44		integral reverse
	(Body Diode) ①			-44		p-n junction diode.
$V_{SD}$	Diode Forward Voltage			-1.6	V	$T_J = 25^{\circ}C$ , $I_S = -7.2A$ , $V_{GS} = 0V$ @
t <sub>rr</sub>	Reverse Recovery Time		47	71	ns	$T_J = 25^{\circ}C, I_F = -7.2A$
Q <sub>rr</sub>	Reverse Recovery Charge		84	130	nC	di/dt = 100A/µs ⊕⑥
t <sub>on</sub>	Forward Turn-On Time	Intrinsic	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)			

#### Notes

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11).
- © Starting  $T_J = 25$ °C, L = 2.8mH  $R_G = 25\Omega$ ,  $I_{AS} = -6.6$ A (See Figure 12)
- ③  $I_{SD} \le -6.6A$ , di/dt ≤ -240A/µs,  $V_{DD} \le V_{(BR)DSS}$ ,

- 4 Pulse width  $\leq 300 \mu s$ ; duty cycle  $\leq 2\%$ .
- © Uses IRF9Z24N data and test conditions.

<sup>\*\*</sup> When mounted on 1" square PCB (FR-4 or G-10 Material).
For recommended footprint and soldering techniques refer to application note #AN-994.

## Qualification Information<sup>†</sup>

			Automotive			
Qualification Level		(per AEC-Q101) <sup>††</sup>				
		qualification.	This part number(s) passed Automotive IR's Industrial and Consumer qualification of by extension of the higher Automotive level.			
Mojeture Sensitivity Level		D PAK	MSL1			
Woisture Serisi	Moisture Sensitivity Level		N/A			
	Machine Model	Class M2(+/-150V) <sup>†††</sup>				
		AEC-Q101-002				
ECD	Human Body Model	Class H1A(+/-500V) †††				
ESD		AEC-Q101-001				
	Charged Device	Class C5(+/-2000V) <sup>†††</sup>				
Model		AEC-Q101-005				
RoHS Complian	nt	Yes				

<sup>†</sup> Qualification standards can be found at International Rectifier's web site: http://www.irf.com/

<sup>††</sup> Exceptions to AEC-Q101 requirements are noted in the qualification report.

<sup>†††</sup> Highest passing voltage

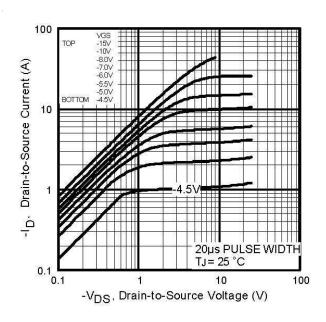


Fig 1. Typical Output Characteristics

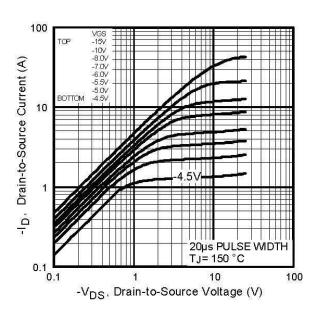


Fig 2. Typical Output Characteristics

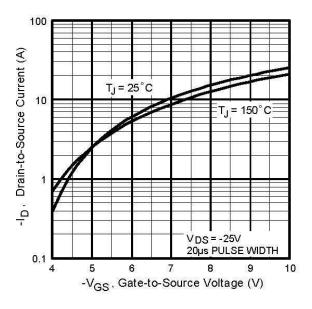
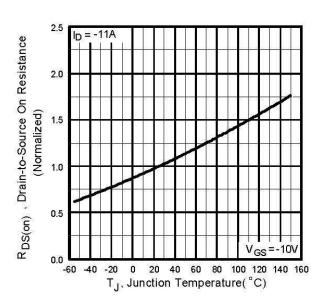
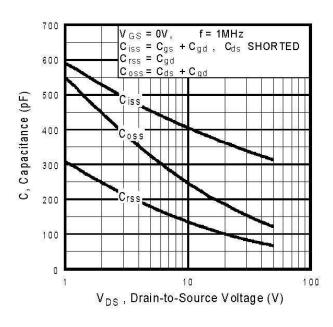


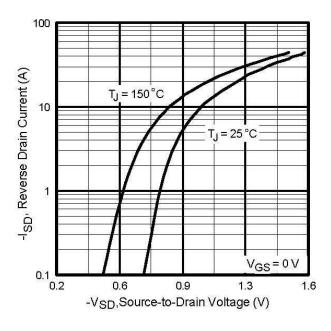
Fig 3. Typical Transfer Characteristics



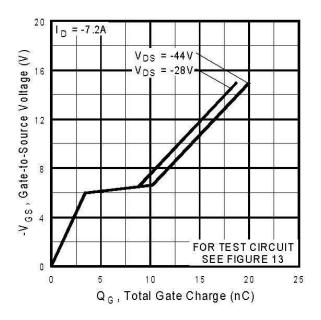
**Fig 4.** Normalized On-Resistance Vs. Temperature



**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 7.** Typical Source-Drain Diode Forward Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage

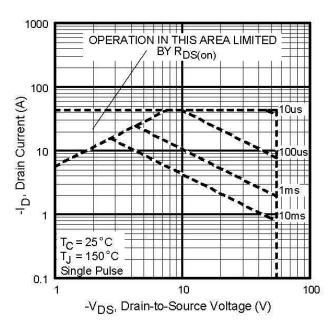
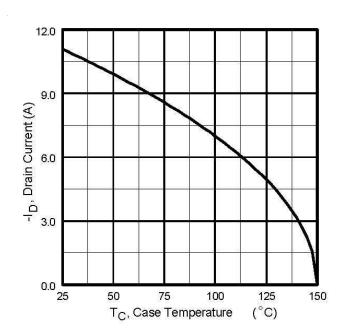


Fig 8. Maximum Safe Operating Area



**Fig 9.** Maximum Drain Current Vs. Case Temperature

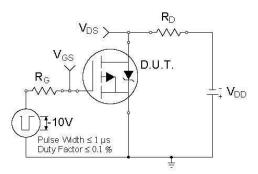


Fig 10a. Switching Time Test Circuit

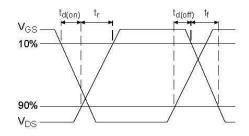


Fig 10b. Switching Time Waveforms

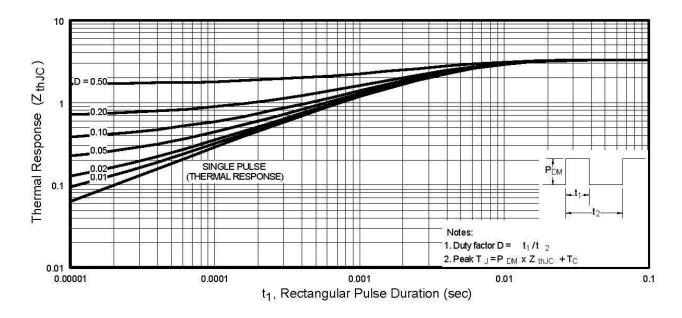


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

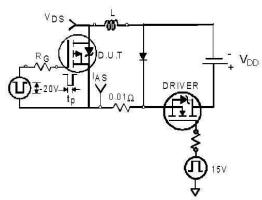


Fig 12a. Unclamped Inductive Test Circuit

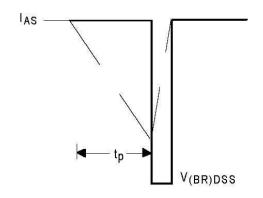


Fig 12b. Unclamped Inductive Waveforms

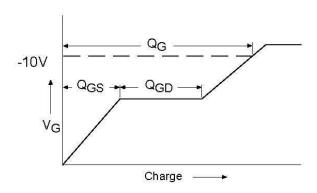
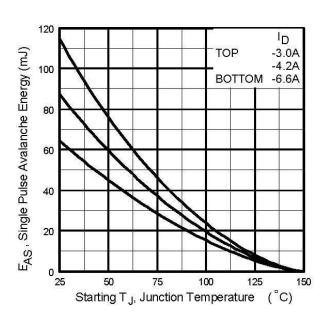


Fig 13a. Basic Gate Charge Waveform



**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current

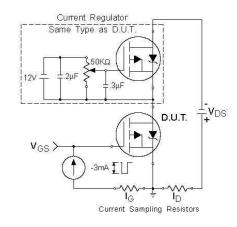
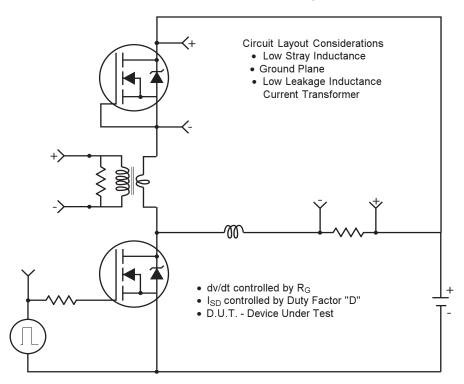
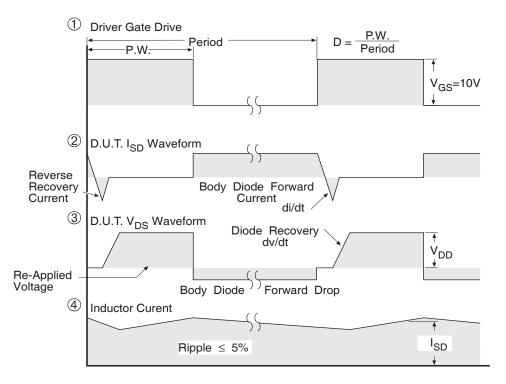


Fig 13b. Gate Charge Test Circuit

## Peak Diode Recovery dv/dt Test Circuit



- \* Reverse Polarity for P-Channel
- \*\* Use P-Channel Driver for P-Channel Measurements

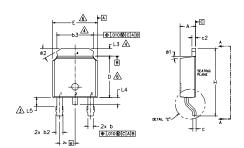


\*\*\*  $V_{GS}$  = 5.0V for Logic Level and 3V Drive Devices

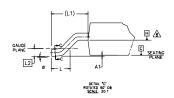
Fig 14 For P Channel HEXFETS

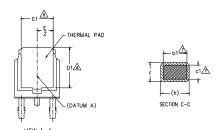
## D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)









#### NOTES:

- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- 2.- DIMENSION ARE SHOWN IN INCHES [MILLIMETERS]
- A- LEAD DIMENSION UNCONTROLLED IN L5.
- A- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
- 5.- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
- DIMENSION D & E DO NOT INCLUDE MOLD FLASH, MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY,
- ⚠ DIMENSION 61 & c1 APPLIED TO BASE METAL ONLY.
- A- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
- 9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

S Y M		DIMEN	ISIONS		Ŋ
В	MILLIM	ETERS	INC	HES	O T E S
0 L	MIN.	MAX.	MIN.	MAX.	E S
Α	2.18	2.39	.086	.094	
Α1	-	0.13	-	.005	
b	0.64	0.89	.025	.035	
ь1	0.65	0.79	.025	.031	7
b2	0.76	1.14	.030	.045	
ь3	4.95	5.46	.195	.215	4
С	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	7
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	6
D1	5.21	-	.205	-	4
Ε	6,35	6.73	,250	.265	6
E1	4.32	-	.170	-	4
е	2,29	2.29 BSC		BSC	
Н	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74	BSC	.108	REF.	
L2	0.51	BSC	.020 BSC		
L3	0.89	1,27	.035	.050	4
L4	-	1.02	-	.040	
L5	1,14	1.52	.045	.060	3
ø	0,	10*	0,	10*	
ø1	0*	15*	0*	15*	
ø2	25'	35*	25*	35*	

#### LEAD ASSIGNMENTS

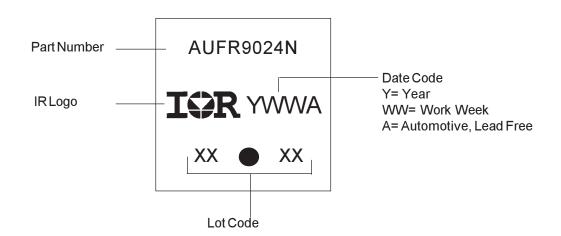
#### **HEXFET**

- 1.- GATE
- 2.- DRAIN 3.- SOURCE
- 4.- DRAIN

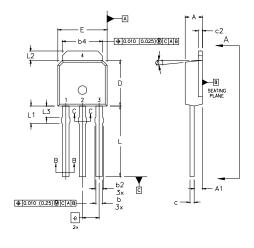
#### IGBT & CoPAK

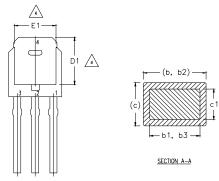
- GATE
- 2.- COLLECTOR
- 4.- COLLECTOR

## D-Pak (TO-252AA) Part Marking Information



## I-Pak (TO-251AA) Package Outline ( Dimensions are shown in millimeters (inches)





#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- DMENSION D & E DO NOT INCLUDE WOLD FLASH, WOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- THERMAL PAD CONTOUR OPTION WITHIN DIMENSION 64, L2, E1 & D1. LEAD DIMENSION UNCONTROLLED IN L3.
- DIMENSION 61, 63 APPLY TO BASE METAL ONLY. OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA.
  CONTROLLING DIMENSION : INCHES.

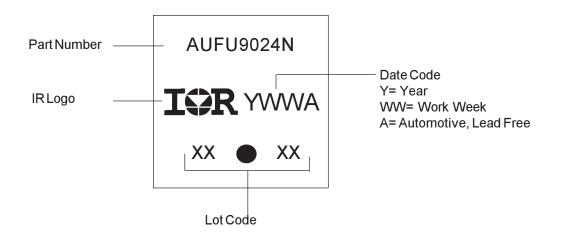
SYMBOL	MILLIM	ÍETERS	INC	HES	
	MIN.	MAX.	MIN.	MAX.	NOTES
A	2.18	2.39	0.086	.094	
A1	0.89	1,14	0.035	0.045	
b	0.64	0.89	0.025	0.035	
ь1	0.64	0.79	0,025	0.031	4
b2	0.76	1,14	0.030	0.045	
b3	0.76	1,04	0.030	0.041	
b4	5.00	5.46	0,195	0.215	4
c	0.46	0.61	0.018	0.024	
c1	0.41	0.56	0.016	0.022	
c2	.046	0.86	0.018	0.035	
D	5.97	6.22	0.235	0.245	3, 4
D1	5.21	-	0,205	-	4
E	6.35	6.73	0.250	0.265	3, 4
E1	4,32	-	0,170	-	4
e	2.	2.29		BSC	
L	8.89	9.60	0.350	0.380	
L1	1.91	2.29	0.075	0.090	
L2	0.89	1.27	0.035	0.050	4
L3	1,14	1.52	0.045	0.060	5
ø1	O*	15'	or or	15*	
1		1	1	1	

LEAD ASSIGNMENTS

#### HEXFET

- 1.- GATE 2.- DRAIN 3.- SOURCE
- 4,- DRAIN

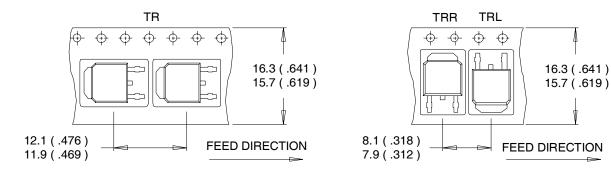
I-Pak (TO-251AA) Part Marking Information



Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

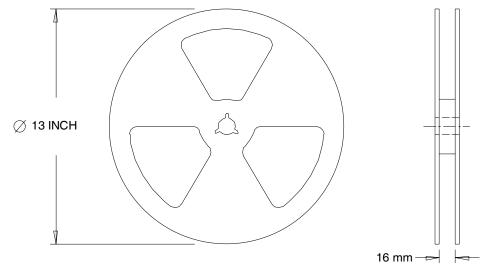
## D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



#### NOTES:

- 1. CONTROLLING DIMENSION: MILLIMETER.
- 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
- 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



### NOTES:

1. OUTLINE CONFORMS TO EIA-481.

# AUIRFR/U9024N

## **Ordering Information**

Base part	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRFR9024N	DPak	Tube	75	AUIRFR9024N
		Tape and Reel	2000	AUIRFR9024NTR
		Tape and Reel Left	3000	AUIRFR9024NTRL
		Tape and Reel Right	3000	AUIRFR9024NTRR
AUIRFU9024N	IPak	Tube	75	AUIRFU9024N

International

TOR Rectifier

## AUIRFR/U9024N

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IR products are neither designed nor intended for use in automotive applications or environments unless the specific IR products are designated by IR as compliant with ISO/TS 16949 requirements and bear a part number including the designation "AU". Buyers acknowledge and agree that, if they use any non-designated products in automotive applications, IR will not be responsible for any failure to meet such requirements

For technical support, please contact IR's Technical Assistance Center <a href="http://www.irf.com/technical-info/">http://www.irf.com/technical-info/</a>

### **WORLD HEADQUARTERS:**

233 Kansas St., El Segundo, California 90245 Tel: (310) 252-7105